

09/504,782

DERWENT-ACC-NO: 2002-477631

DERWENT-WEEK: 200251

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TITLE: Nitride semiconductor device and
manufacturing method
thereof

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PRIORITY-DATA: 2000KR-0033763 (June 20, 2000)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE
PAGES MAIN-IPC		
KR 2002000898 A	January 9, 2002	N/A
H01L 029/772		001

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO
APPL-DATE		
KR2002000898A	N/A	2000KR-0033763
June 20, 2000		

INT-CL (IPC): H01L029/772

ABSTRACTED-PUB-NO: KR2002000898A

BASIC-ABSTRACT:

NOVELTY - A method for manufacturing a nitride semiconductor device is provided to easily grow an indium-containing compound layer like an $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{N}$ layer, by growing $\text{In}_x\text{Ga}_{1-x}\text{N}$ as a buffer layer so that mole density of indium is easily increased or decreased.

DETAILED DESCRIPTION - The buffer layer(12) is stacked on a substrate(11). A semiconductor layer group including at least a semiconductor layer is stacked on the buffer layer, wherein the buffer layer includes an indium-containing nitride. A nitride semiconductor device includes the substrate, the buffer layer and the semiconductor layer.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: NITRIDE SEMICONDUCTOR DEVICE
MANUFACTURE METHOD

DERWENT-CLASS: L03 U11 U12

CPI-CODES: L04-A02B1; L04-A02C1;

EPI-CODES: U11-C05B5; U12-E01A1;

SECONDARY-ACC-NO:

CPI Secondary Accession Numbers: C2002-135647

제2 상부 클래드층 P형 $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{N}$ ($0 < x < 1, 0 < y < 1$)	17
제1 상부 클래드층 P형 $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{N}$ ($0 < x < 1, 0 < y < 1$)	16
활성층 $\text{In}_x\text{Ga}_{1-x}\text{N}$ ($0 < x < 1$)	15
제2 하부 클래드층 n형 $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{N}$ ($0 < x < 1, 0 < y < 1$)	14
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